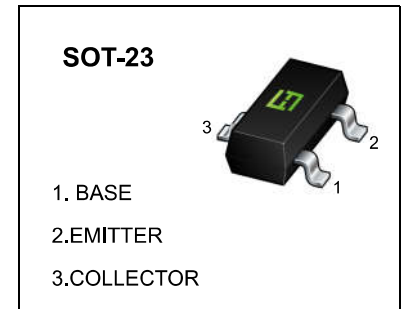


FEATURES

- Epitaxial planar die construction
- Complementary PNP Type available(MMBT2907A)



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	75	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	600	mA
P _C	Collector Dissipation	300	mW
R _{θJA}	Thermal Resistance, Junction to Ambient	417	°C/W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

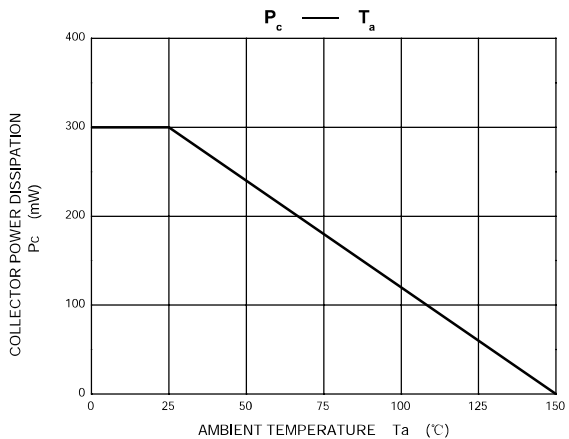
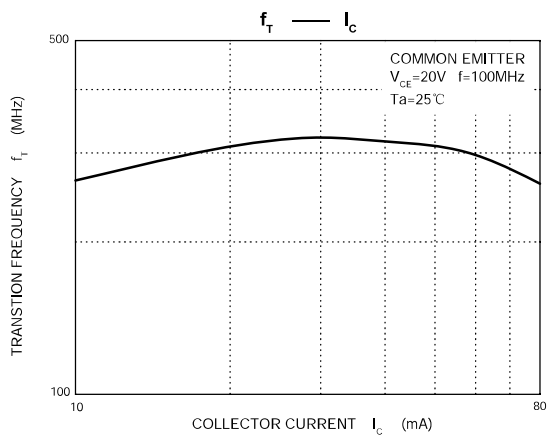
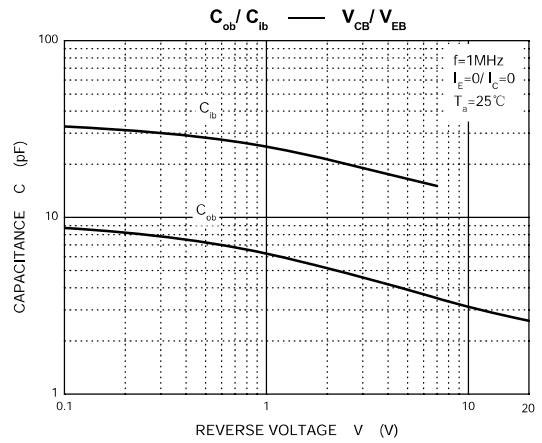
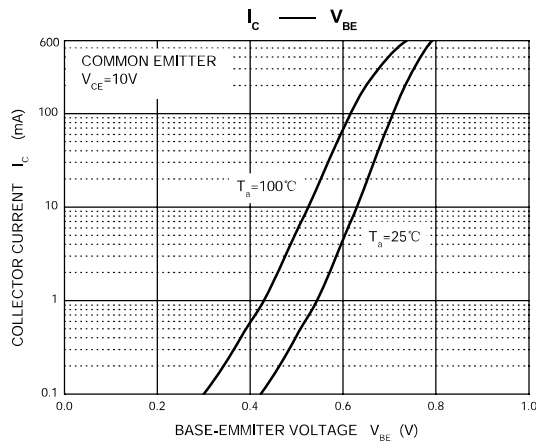
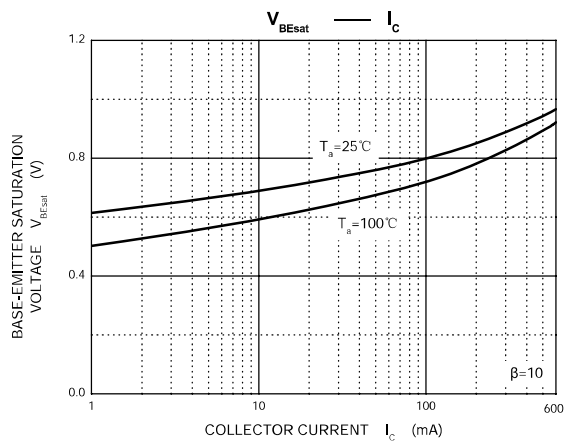
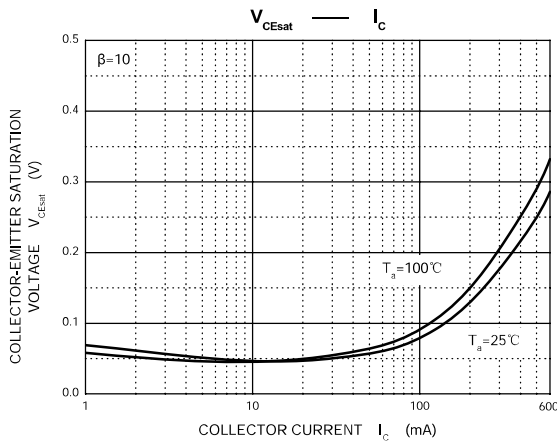
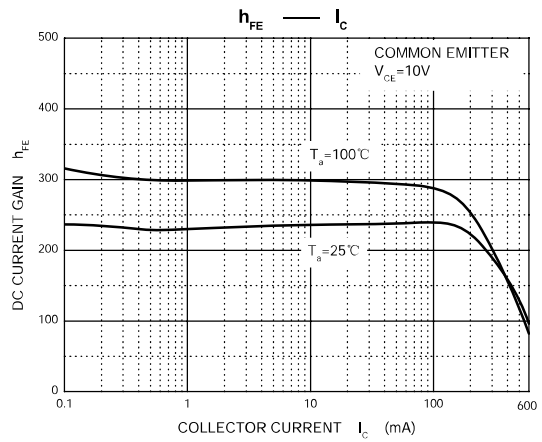
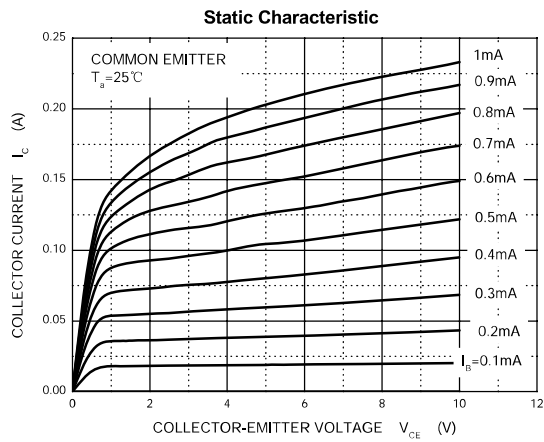
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E =0	75			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C = 10mA, I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.01	μA
Collector cut-off current	I _{CEX}	V _{CE} =30V, V _{BE(off)} =3V			0.01	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 3V, I _C =0			0.1	μA
DC current gain	h _{FE(1)} *	V _{CE} =10V, I _C = 150mA	100		300	
	h _{FE(2)}	V _{CE} =10V, I _C = 0.1mA	40			
	h _{FE(3)} *	V _{CE} =10V, I _C = 500mA	42			
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =500 mA, I _B = 50mA I _C =150 mA, I _B =15mA			1 0.3	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =500 mA, I _B = 50mA I _C =150 mA, I _B =15mA			2.0 1.2	V
Transition frequency	f _T	V _{CE} =20V, I _C = 20mA, f=100MHz	300			MHz
Delay time	t _d	V _{CC} =30V, V _{BE(off)} =-0.5V			10	ns
Rise time	t _r	I _C =150mA, I _{B1} = 15mA			25	ns
Storage time	t _s	V _{CC} =30V, I _C =150mA			225	ns
Fall time	t _f	I _{B1} =-I _{B2} =15mA			60	ns

*pulse test: Pulse Width ≤300μs, Duty Cycles ≤ 2.0%.

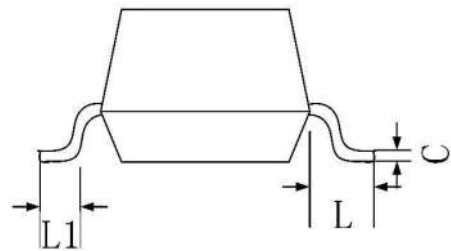
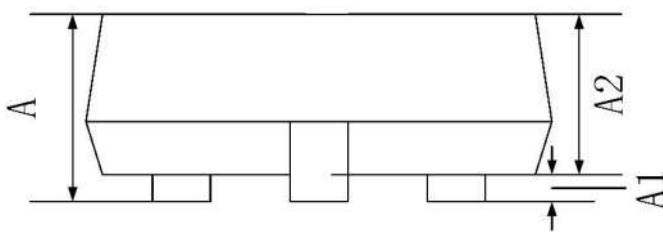
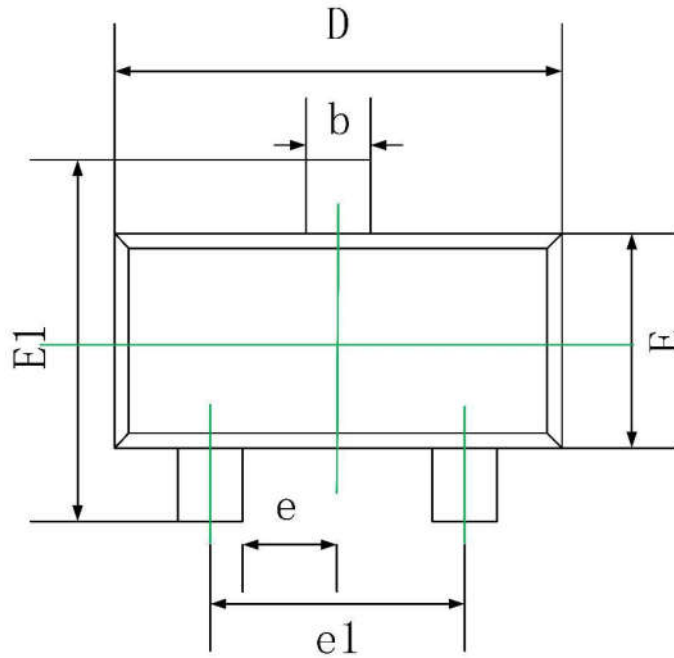
CLASSIFICATION OF h_{FE(1)}

RANK	L	H
RANGE	100 - 200	200 - 300
MARKING	1P	

Typical Characteristics



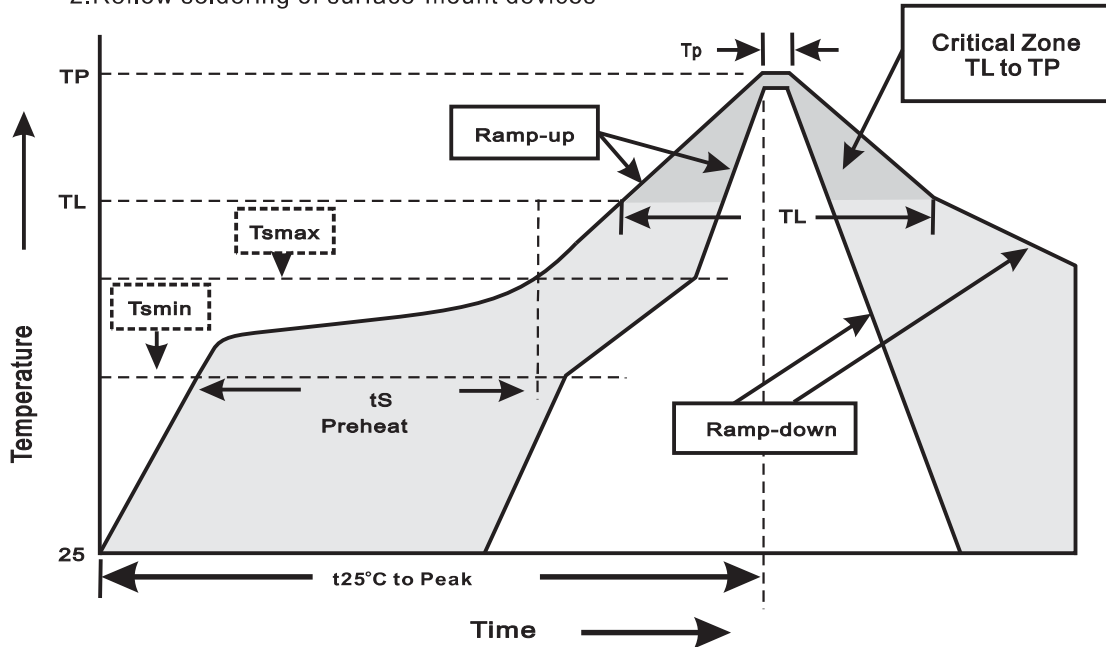
SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(TL to TP)	<3°C/sec
Preheat -Temperature Min(Tsmin) -Temperature Max(Tsmax) -Time(min to max)(ts)	150°C 200°C 60~120sec
Tsmax to TL -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(TL) -Time(tL)	217°C 60~260sec
Peak Temperature(TP)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(tp)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes